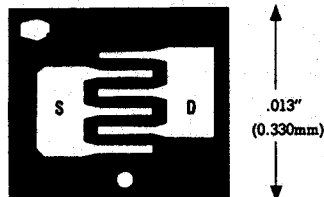


CHIP NUMBER
FN22.2



Die Size: 13 x 16 (mils)
0.330 x 0.406(mm)
Pad Size: 4 x 6 (mils)
0.102 x 0.152(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
$B_{V_{GS}}$	-40	-60	-80	V	$V_{DS} = 0, I_G = 1\mu A$
I_{DSS}	0.1	3.0	10.0	mA	$V_{DS} = 20V, V_{GS} = 0$
g_{fs}	0.5	1.7	3.0	mmho	$V_{DS} = 20V, V_{GS} = 0$
I_{GSS}		-10	-100	pA	$V_{GS} = -30V, V_{DS} = 0$
r_{DS}	300	500	2000	Ω	$V_{DS} = 100mV, V_{GS} = 0$
$V_{GS(off)}$	-0.5	-2.5	-6.0	V	$V_{DS} = 20V, I_D = 1nA$
C_{rss}	0.8	1.2	1.8	pF	$V_{DS} = 20V, V_{GS} = 0, f = 1MHz$
C_{iss}	3.0	4.0	5.0	pF	$V_{DS} = 20V, V_{GS} = 0, f = 1MHz$
$\bar{e}_n$		30	50	nV/ $\sqrt{Hz}$	$V_{DS} = 20V, V_{GS} = 0, f = 100Hz$

TYPICAL DEVICE TYPES: 2N3684A, 2N4338, 2N4341, 2N4302 - 2N4304

CHIP TYPE FN22.2

